

## Inchange Semiconductor

## Product Specification

## Silicon PNP Power Transistors

## 3CD6D

## DESCRIPTION

- With TO-3 package
- Low collector saturation voltage

## APPLICATIONS

- For power amplifier and low speed switching applications

## PINNING(see Fig.2)

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | Base        |
| 2   | Emitter     |
| 3   | Collector   |

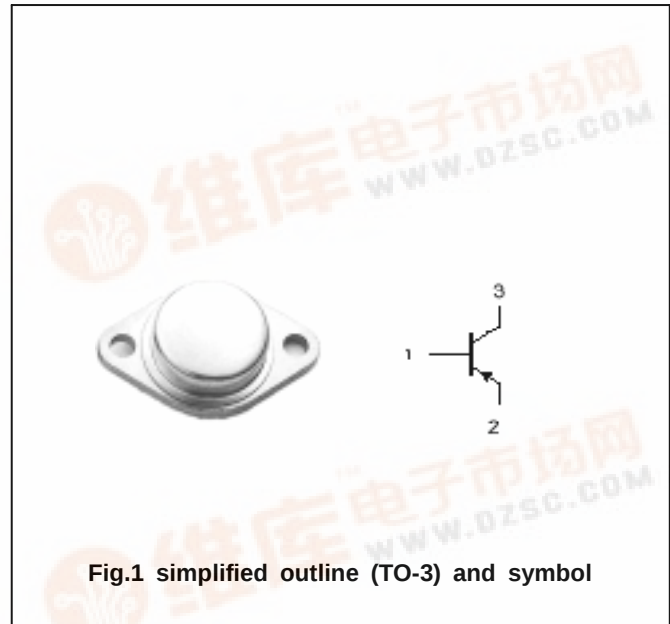


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings( $T_a = -$ )

| SYMBOL    | PARAMETER                   | CONDITIONS     | VALUE   | UNIT |
|-----------|-----------------------------|----------------|---------|------|
| $V_{CBO}$ | Collector-base voltage      | Open emitter   | -110    | V    |
| $V_{CEO}$ | Collector-emitter voltage   | Open base      | -110    | V    |
| $V_{EBO}$ | Emitter-base voltage        | Open collector | -4      | V    |
| $I_C$     | Collector current           |                | -5      | A    |
| $P_C$     | Collector power dissipation | $T_c = 75$     | 50      | W    |
| $T_j$     | Junction temperature        |                | 150     |      |
| $T_{stg}$ | Storage temperature         |                | -55~150 |      |

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

| SYMBOL               | PARAMETER                            | CONDITIONS                                    | MIN  | TYP. | MAX  | UNIT |
|----------------------|--------------------------------------|-----------------------------------------------|------|------|------|------|
| V <sub>(BR)CEO</sub> | Collector-emitter breakdown voltage  | I <sub>C</sub> =-10mA ; I <sub>B</sub> =0     | -110 |      |      | V    |
| V <sub>(BR)EBO</sub> | Emitter-base breakdown voltage       | I <sub>E</sub> =-1mA ; I <sub>B</sub> =0      | -4   |      |      | V    |
| V <sub>CEsat</sub>   | Collector-emitter saturation voltage | I <sub>C</sub> =-2.5A; I <sub>B</sub> =-0.5A  |      | -1.0 | -1.5 | V    |
| V <sub>BEsat</sub>   | Base-emitter saturation voltage      | I <sub>C</sub> =-2.5A; I <sub>B</sub> =-0.5A  |      |      | -2.0 | V    |
| I <sub>CBO</sub>     | Collector cut-off current            | V <sub>CB</sub> =-110V; I <sub>E</sub> =0     |      |      | -0.1 | mA   |
| I <sub>CEO</sub>     | Collector cut-off current            | V <sub>CE</sub> =-110V; I <sub>E</sub> =0     |      |      | -1.0 | mA   |
| I <sub>EBO</sub>     | Emitter cut-off current              | V <sub>EB</sub> =-4V; I <sub>C</sub> =0       |      |      | -0.1 | mA   |
| h <sub>FE</sub>      | DC current gain                      | I <sub>C</sub> =-2.5A ; V <sub>CE</sub> =-10V | 10   |      | 180  |      |

固电半导体

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PACKAGE OUTLINE

